# VS-1EFH01-M3

**Vishay Semiconductors** 

# Hyperfast Rectifier, 1 A FRED Pt®



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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	1 A			
V <sub>R</sub>	100 V			
V <sub>F</sub> at I <sub>F</sub> (typ. 125 °C)	0.74 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

### FEATURES

• Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

## **MECHANICAL DATA**

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub>		100	V	
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	٨	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	35	A	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C	

Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	100	-	-	
Forward voltage		I <sub>F</sub> = 1 A	-	0.87	0.93	V
r orward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C	-	0.74	0.8	
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	2	μA
neverse leakage current i	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μΑ
Junction capacitance	CT	V <sub>R</sub> = 100 V	-	5	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A}$	/µs, V <sub>R</sub> = 30 V	-	24	-	
Reverse recovery time	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 1 A$	-	16	-	ns
		T <sub>J</sub> = 125 °C		-	23	-	
Deals reasoning as meant		T <sub>J</sub> = 25 °C		-	1.6	-	Α
Peak recovery current	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 160 V	-	2.5	-		
	T <sub>J</sub> = 25 °C		-	13	-	nC	
neverse recovery charge	Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	30	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	+175	°C
Thermal resistance, junction to mount	R <sub>thJM</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W
Approximate unight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)	МАН			

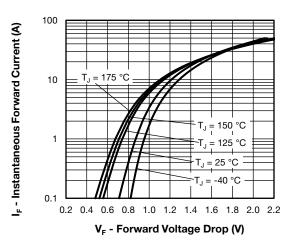


Fig. 1 - Typical Forward Voltage Drop Characteristics

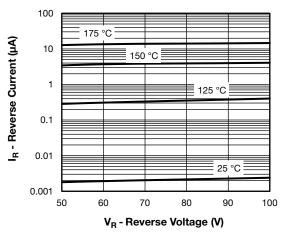


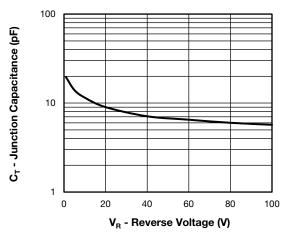
Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

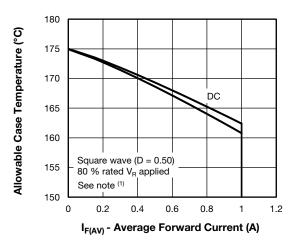


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

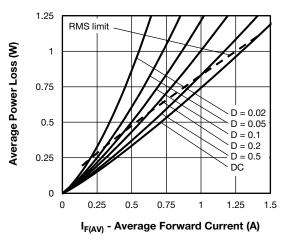
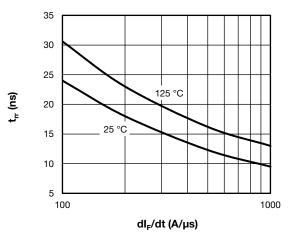


Fig. 5 - Forward Power Loss Characteristics





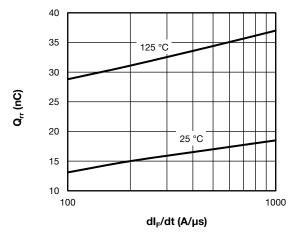


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ at \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (1 \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ at \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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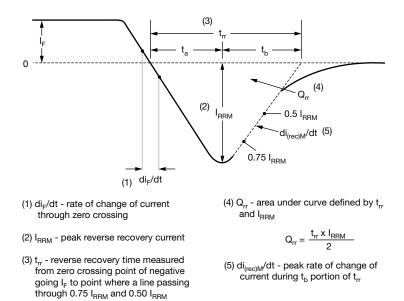
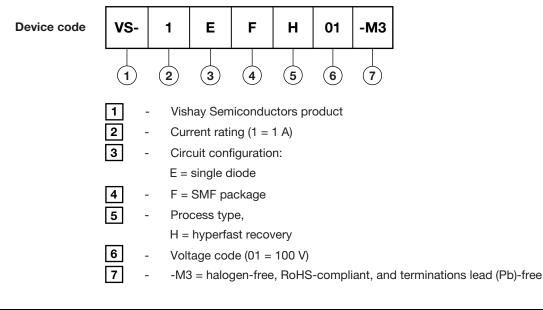


Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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extrapolated to zero current.

ORDERING INFORMATION (Example)							
PREFERRED P/N	ERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-1EFH01-M3/I	10 000	10 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96012			

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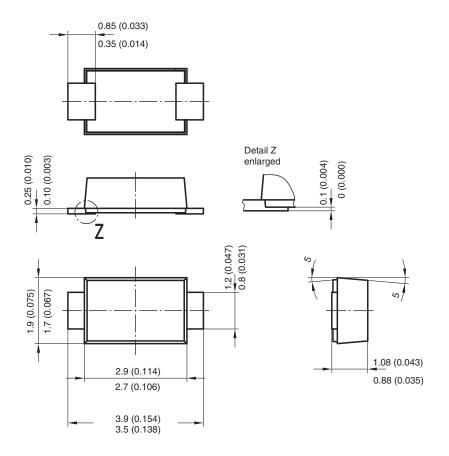
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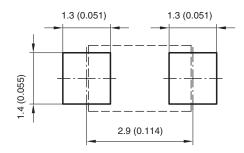
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# SMF (DO-219AB)

### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



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